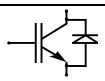

Vorläufige Daten
Preliminary data

Elektrische Eigenschaften / Electrical properties

Höchstzulässige Werte / Maximum rated values

Diode Gleichrichter/ Diode Rectifier				
Periodische Rückw. Spitzensperrspannung repetitive peak reverse voltage		V_{RRM}	1600	V
Gleichrichter Ausgang Grenzeffektivstrom maximum RMS current at Rectifier output		I_{RMSmax}	t.b.d.	A
Dauergleichstrom DC forward current	T_C = 80°C	I_d	40	A
Stoßstrom Grenzwert surge forward current	t_P = 10 ms, T_{vj} = 25°C t_P = 10 ms, T_{vj} = 150°C	I_{FSM}	315 260	A A
Grenzlastintegral I^2t - value	t_P = 10 ms, T_{vj} = 25°C t_P = 10 ms, T_{vj} = 150°C	I^2t	500 340	A^2s A^2s
Transistor Wechselrichter/ Transistor Inverter				
Kollektor-Emitter-Sperrspannung collector-emitter voltage		V_{CES}	1200	V
Kollektor-Dauergleichstrom DC-collector current	Tc = 80 °C T_C = 25 °C	$I_{C,nom.}$ I_C	40 55	A A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	t_P = 1 ms, T_C = 80 °C	I_{CRM}	80	A
Gesamt-Verlustleistung total power dissipation	T_C = 25°C	P_{tot}	200	W
Gate-Emitter-Spitzenspannung gate-emitter peak voltage		V_{GES}	+/- 20V	V
Diode Wechselrichter/ Diode Inverter				
Dauergleichstrom DC forward current	Tc = 80 °C	I_F	40	A
Periodischer Spitzenstrom repetitive peak forw. current	t_P = 1 ms	I_{FRM}	80	A
Grenzlastintegral I^2t - value	V_R = 0V, t_p = 10ms, T_{vj} = 125°C	I^2t	320	A^2s
Transistor Brems-Chopper/ Transistor Brake-Chopper				
Kollektor-Emitter-Sperrspannung collector-emitter voltage		V_{CES}	1200	V
Kollektor-Dauergleichstrom DC-collector current	T_C = 80 °C T_C = 25 °C	$I_{C,nom.}$ I_C	40 55	A A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	t_P = 1 ms, T_C = 80°C	I_{CRM}	80	A
Gesamt-Verlustleistung total power dissipation	T_C = 25°C	P_{tot}	200	W
Gate-Emitter-Spitzenspannung gate-emitter peak voltage		V_{GES}	+/- 20V	V
Diode Brems-Chopper/ Diode Brake-Chopper				
Dauergleichstrom DC forward current	Tc = 80 °C	I_F	15	A
Periodischer Spitzenstrom repetitive peak forw. current	t_P = 1 ms	I_{FRM}	30	A

prepared by: Andreas Schulz	date of publication:06.03.2001
approved by: Hornkamp	revision: 1

Vorläufige Daten
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Modul Isolation/ Module Isolation

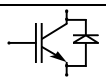
Isolations-Prüfspannung insulation test voltage	RMS, f = 50 Hz, t = 1 min. NTC connected to Baseplate	V_{ISOL}	2,5	kV

Elektrische Eigenschaften / Electrical properties

Charakteristische Werte / Characteristic values

Diode Gleichrichter/ Diode Rectifier			**min.**	**typ.**	**max.**	
Durchlaßspannung forward voltage	T_{vj} = 150°C, I_F = 40 A	V_F	-	1,2	-	V
Schleusenspannung threshold voltage	T_{vj} = 150°C	$V_{(TO)}$	-	-	0,8	V
Ersatzwiderstand slope resistance	T_{vj} = 150°C	r_T	-	-	10,5	mΩ
Sperrstrom reverse current	T_{vj} = 150°C, V_R = 1600 V	I_R	-	2	-	mA
Modul Leitungswiderstand, Anschlüsse-Chip lead resistance, terminals-chip	T_C = 25°C	$R_{AA'+CC'}$	-	4	-	mΩ

Transistor Wechselrichter/ Transistor Inverter			**min.**	**typ.**	**max.**	
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	V_{GE} = 15V, T_{vj} = 25°C, I_C = 40 A V_{GE} = 15V, T_{vj} = 125°C, I_C = 40 A	$V_{CE\ sat}$	- -	1,8 2,15	2,3 -	V V
Gate-Schwellenspannung gate threshold voltage	V_{CE} = V_{GE}, T_{vj} = 25°C, I_C = 1,5 mA	$V_{GE(TO)}$	5,0	5,8	6,5	V
Eingangskapazität input capacitance	f = 1MHz, T_{vj} = 25°C V_{CE} = 25 V, V_{GE} = 0 V	C_{ies}	-	2,5	-	nF
Kollektor-Emitter Reststrom collector-emitter cut off current	V_{GE} = 0V, T_{vj} = 25°C, V_{CE} = 1200 V	I_{CES}	-	-	5	mA
Gate-Emitter Reststrom gate-emitter leakage current	V_{CE} = 0V, V_{GE} =20V, T_{vj} =25°C	I_{GES}	-	-	400	nA
Einschaltverzögerungszeit (ind. Last) turn on delay time (inductive load)	I_C = I_{Nenn}, V_{CC} = 600 V V_{GE} = ±15V, T_{vj} = 25°C, R_G = 27 Ohm V_{GE} = ±15V, T_{vj} = 125°C, R_G = 27 Ohm	$t_{d,on}$	- -	85 90	- -	ns ns
Anstiegszeit (induktive Last) rise time (inductive load)	I_C = I_{Nenn}, V_{CC} = 600 V V_{GE} = ±15V, T_{vj} = 25°C, R_G = 27 Ohm V_{GE} = ±15V, T_{vj} = 125°C, R_G = 27 Ohm	t_r	- -	30 45	- -	ns ns
Abschaltverzögerungszeit (ind. Last) turn off delay time (inductive load)	I_C = I_{Nenn}, V_{CC} = 600 V V_{GE} = ±15V, T_{vj} = 25°C, R_G = 27 Ohm V_{GE} = ±15V, T_{vj} = 125°C, R_G = 27 Ohm	$t_{d,off}$	- -	420 520	- -	ns ns
Fallzeit (induktive Last) fall time (inductive load)	I_C = I_{Nenn}, V_{CC} = 600 V V_{GE} = ±15V, T_{vj} = 25°C, R_G = 27 Ohm V_{GE} = ±15V, T_{vj} = 125°C, R_G = 27 Ohm	t_f	- -	65 90	- -	ns ns
Einschaltverlustenergie pro Puls turn-on energy loss per pulse	I_C = I_{Nenn}, V_{CC} = 600 V V_{GE} = ±15V, T_{vj} = 125°C, R_G = 27 Ohm L_S = 45 nH	E_{on}	-	6	-	mWs
Abschaltverlustenergie pro Puls turn-off energy loss per pulse	I_C = I_{Nenn}, V_{CC} = 600 V V_{GE} = ±15V, T_{vj} = 125°C, R_G = 27 Ohm L_S = 45 nH	E_{off}	-	4,2	-	mWs
Kurzschlußverhalten SC Data	t_P ≤ 10µs, V_{GE} ≤ 15V, R_G = 27 Ohm T_{vj}≤125°C, V_{CC} = 720 V	I_{SC}	-	160	-	A

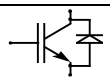


Vorläufige Daten
Preliminary data

Elektrische Eigenschaften / Electrical properties

Charakteristische Werte / Characteristic values

			min.	typ.	max.	
Modulinduktivität stray inductance module		$L_{\sigma CE}$	-	-	100	nH
Modul Leitungswiderstand, Anschlüsse-Chip lead resistance, terminals-chip	T_C = 25°C	$R_{CC'+EE'}$	-	7	-	mΩ
Diode Wechselrichter/ Diode Inverter			**min.**	**typ.**	**max.**	
Durchlaßspannung forward voltage	V_{GE} = 0V, T_{vj} = 25°C, I_F = 40 A	V_F	-	1,75	2,3	V
	V_{GE} = 0V, T_{vj} = 125°C, I_F = 40 A		-	1,75	-	V
Rückstromspitze peak reverse recovery current	I_F=I_{Nenn}, - di_F/dt = 900 A/µs					
	V_{GE} = -10V, T_{vj} = 25°C, V_R = 600 V	I_{RM}	-	39	-	A
	V_{GE} = -10V, T_{vj} = 125°C, V_R = 600 V		-	38	-	A
Sperrverzögerungsladung recovered charge	I_F=I_{Nenn}, - di_F/dt = 900 A/µs					
	V_{GE} = -10V, T_{vj} = 25°C, V_R = 600 V	Q_r	-	4,2	-	µAs
	V_{GE} = -10V, T_{vj} = 125°C, V_R = 600 V		-	7,8	-	µAs
Abschaltenergie pro Puls reverse recovery energy	I_F=I_{Nenn}, - di_F/dt = 900 A/µs					
	V_{GE} = -10V, T_{vj} = 25°C, V_R = 600 V	E_{RQ}	-	1,35	-	mWs
	V_{GE} = -10V, T_{vj} = 125°C, V_R = 600 V		-	2,8	-	mWs
Transistor Brems-Chopper/ Transistor Brake-Chopper			**min.**	**typ.**	**max.**	
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	V_{GE} = 15V, T_{vj} = 25°C, I_C = 40 A	$V_{CE\ sat}$	-	1,8	2,3	V
	V_{GE} = 15V, T_{vj} = 125°C, I_C = 40 A		-	2,15	-	V
Gate-Schwellenspannung gate threshold voltage	V_{CE} = V_{GE}, T_{vj} = 25°C, I_C = 1,5 mA	$V_{GE(TO)}$	5,0	5,8	6,5	V
Eingangskapazität input capacitance	f = 1MHz, T_{vj} = 25°C V_{CE} = 25 V, V_{GE} = 0 V	C_{ies}	-	2,5	-	nF
Kollektor-Emitter Reststrom collector-emitter cut off current	V_{GE} = 0V, T_{vj} = 25°C, V_{CE} = 1200 V	I_{CES}	-	5,0	-	mA
Gate-Emitter Reststrom gate-emitter leakage current	V_{CE} = 0V, V_{GE} = 20V, T_{vj} = 25°C	I_{GES}	-	-	400	nA
Schaltverluste und -bedingungen Switching losses and conditions	siehe Wechselrichter in diesem Datenblatt see inverter in this datasheet					
Diode Brems-Chopper/ Diode Brake-Chopper			**min.**	**typ.**	**max.**	
Durchlaßspannung forward voltage	T_{vj} = 25°C, I_F = 40 A	V_F	-	2,35	2,8	V
	T_{vj} = 125°C, I_F = 40 A		-	2,55	-	V
Schaltverluste und -bedingungen Switching losses and conditions	siehe Wechselrichter in Dbl FP15R12KE3 see inverter in datasheet FP15R12KE3					
NTC-Widerstand/ NTC-Thermistor			**min.**	**typ.**	**max.**	
Nennwiderstand rated resistance	T_C = 25°C	R_{25}	-	5	-	kΩ
Abweichung von R_{100} deviation of R_{100}	T_C = 100°C, R_{100} = 493 Ω	ΔR/R	-5		5	%
Verlustleistung power dissipation	T_C = 25°C	P_{25}			20	mW
B-Wert B-value	$R_2 = R_1 \exp [B(1/T_2 - 1/T_1)]$	$B_{25/50}$		3375		K



Vorläufige Daten
Preliminary data

Thermische Eigenschaften / Thermal properties

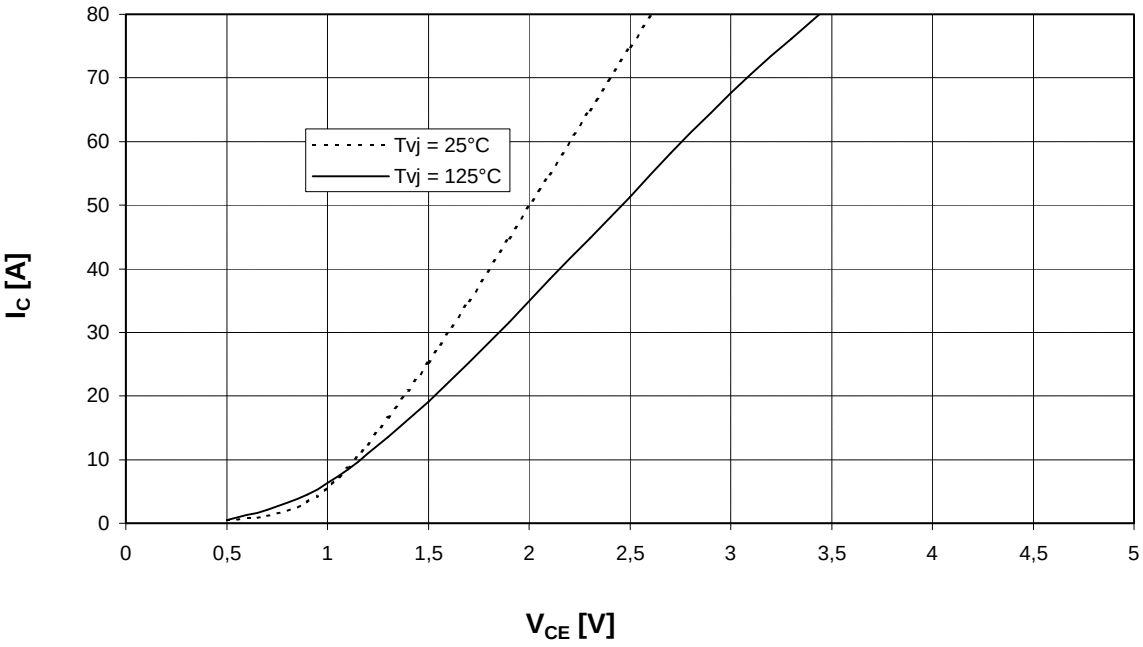
				min.	typ.	max.	
Innerer Wärmewiderstand thermal resistance, junction to case	Gleichr. Diode/ Rectif. Diode		R_{thJC}	-	-	1	K/W
	Trans. Wechsr./ Trans. Inverter			-	-	0,6	K/W
	Diode Wechsr./ Diode Inverter			-	-	0,95	K/W
	Trans. Bremse/ Trans. Brake			-	-	0,6	K/W
	Diode Bremse/ Diode Brake			-	-	1,5	K/W
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	Gleichr. Diode/ Rectif. Diode	λ_{Paste}=1W/m*K	R_{thCK}	-	0,04	-	K/W
	Trans. Wechsr./ Trans. Inverter	λ_{grease}=1W/m*K		-	0,02	-	K/W
	Diode Wechsr./ Diode Inverter			-	0,04	-	K/W
Höchstzulässige Sperrschichttemperatur maximum junction temperature			T_{vj}	-	-	150	°C
Betriebstemperatur operation temperature			T_{op}	-40	-	125	°C
Lagertemperatur storage temperature			T_{stg}	-40	-	125	°C

Mechanische Eigenschaften / Mechanical properties

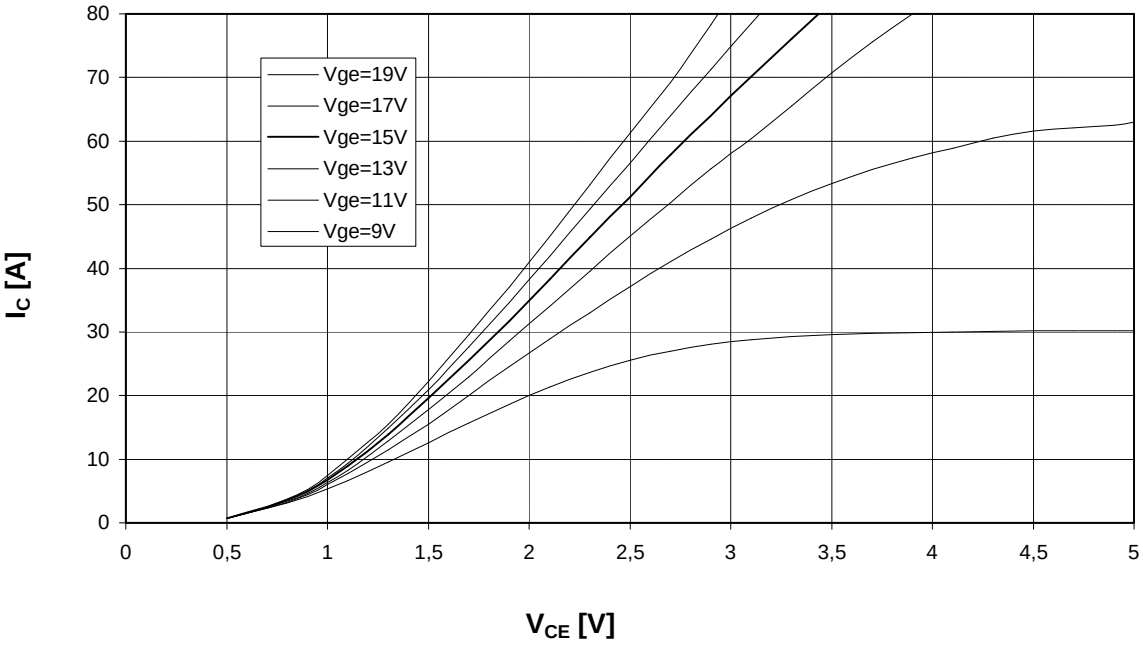
Innere Isolation internal insulation			Al_2O_3	
CTI comperative tracking index			225	
Anzugsdrehmoment f. mech. Befestigung mounting torque		M	3 ±10%	Nm
Gewicht weight		G	300	g

Vorläufige Daten
Preliminary data

Ausgangskennlinienfeld Wechselr. (typisch) $I_C = f(V_{CE})$
Output characteristic Inverter (typical) $V_{GE} = 15\ V$



Ausgangskennlinienfeld Wechselr. (typisch) $I_C = f(V_{CE})$
Output characteristic Inverter (typical) $T_{vj} = 125°C$



Vorläufige Daten
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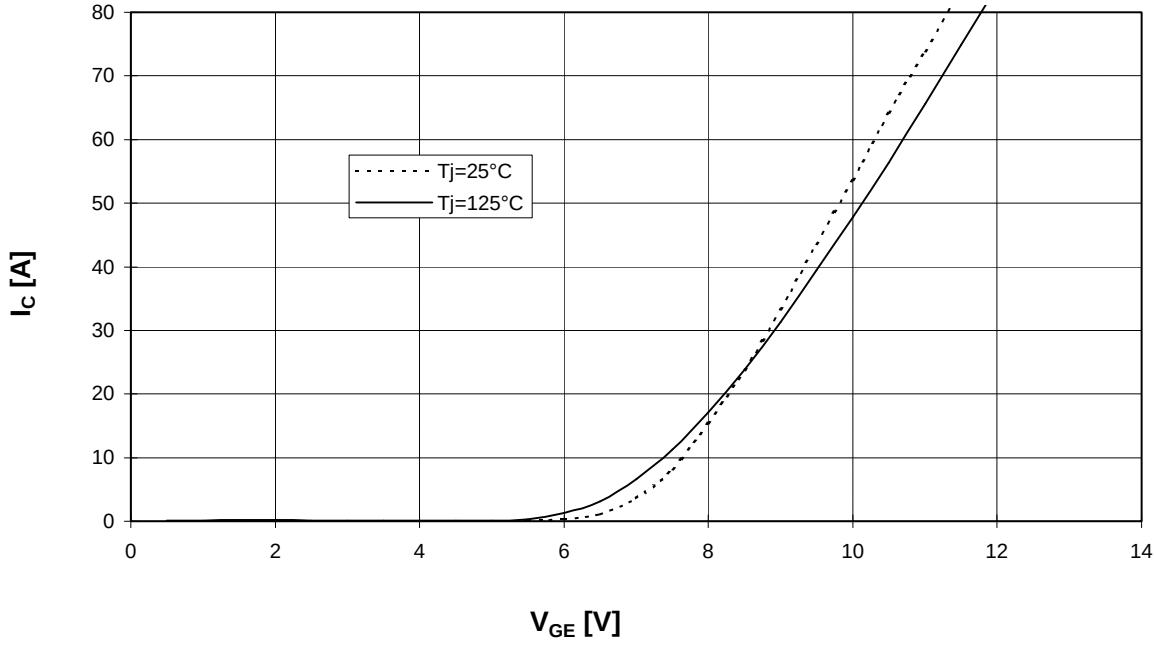
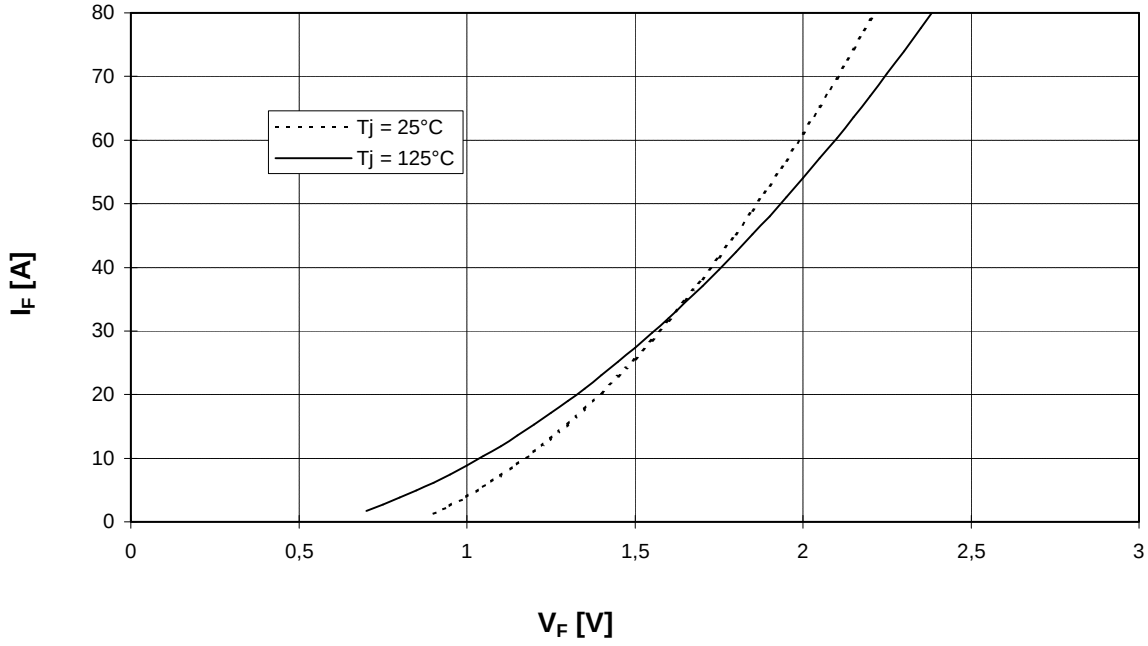
Übertragungscharakteristik Wechselr. (typisch) $I_C = f(V_{GE})$
Transfer characteristic Inverter (typical) $V_{CE} = 20\ V$

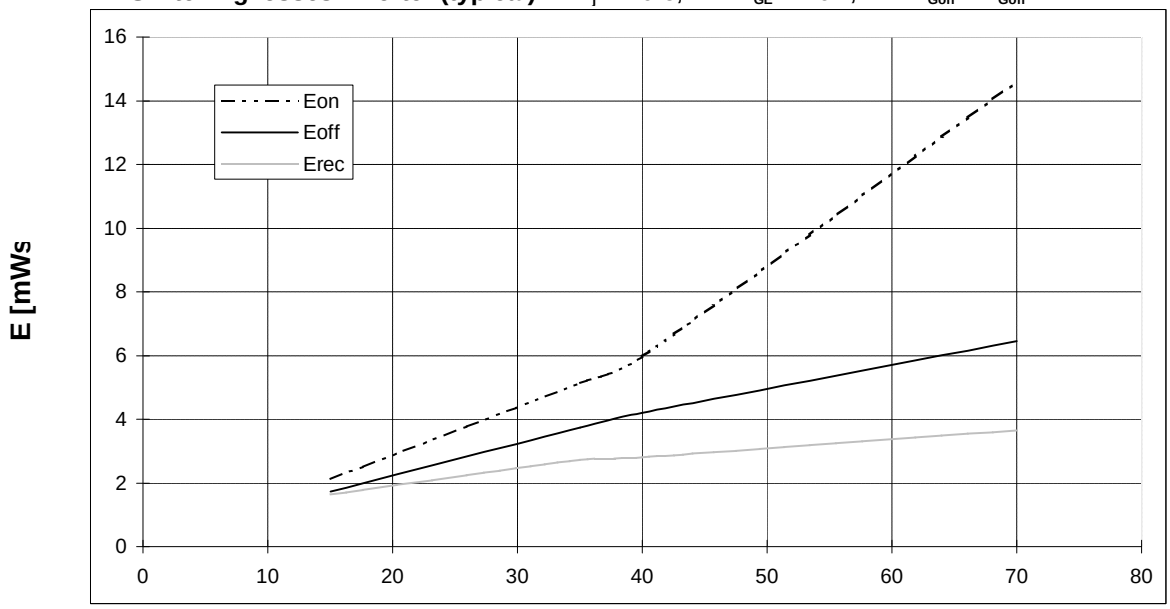


Durchlaßkennlinie der Freilaufdiode Wechselr. (typisch) $I_F = f(V_F)$
Forward characteristic of FWD Inverter (typical)

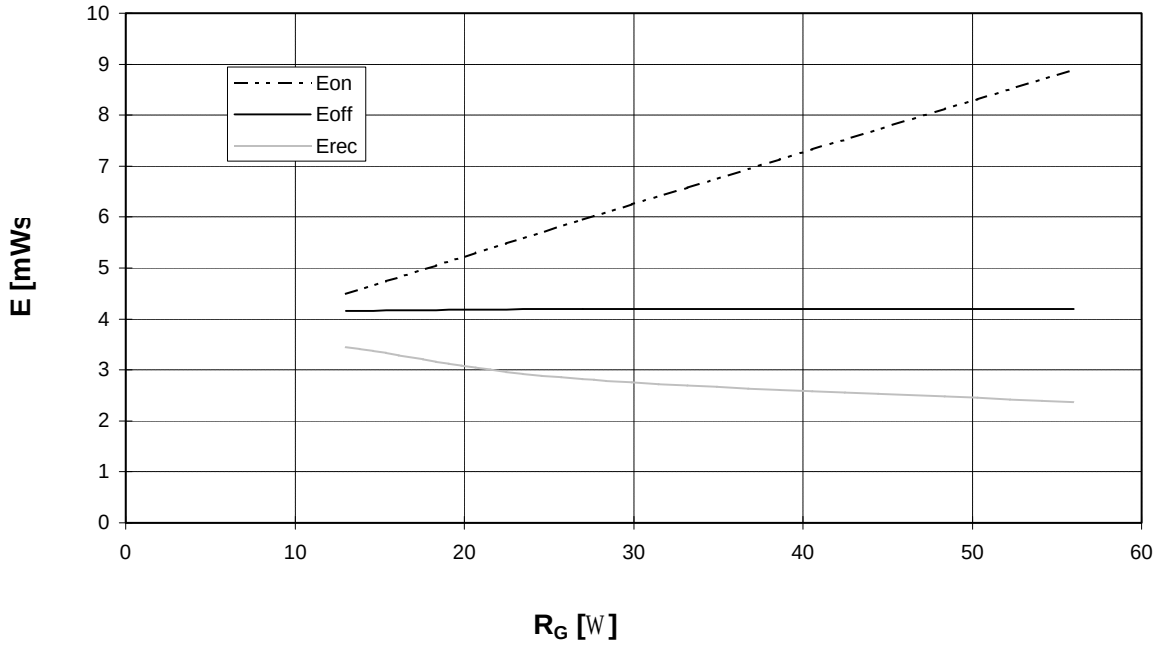


Vorläufige Daten
Preliminary data

Schaltverluste Wechselr. (typisch) $E_{on} = f(I_C)$, $E_{off} = f(I_C)$, $E_{rec} = f(I_C)$ V_{CC} = **600 V**
Switching losses Inverter (typical) T_j = 125°C, V_{GE} = ±15 V, $R_{Gon} = R_{Goff}$ = **27 Ohm**

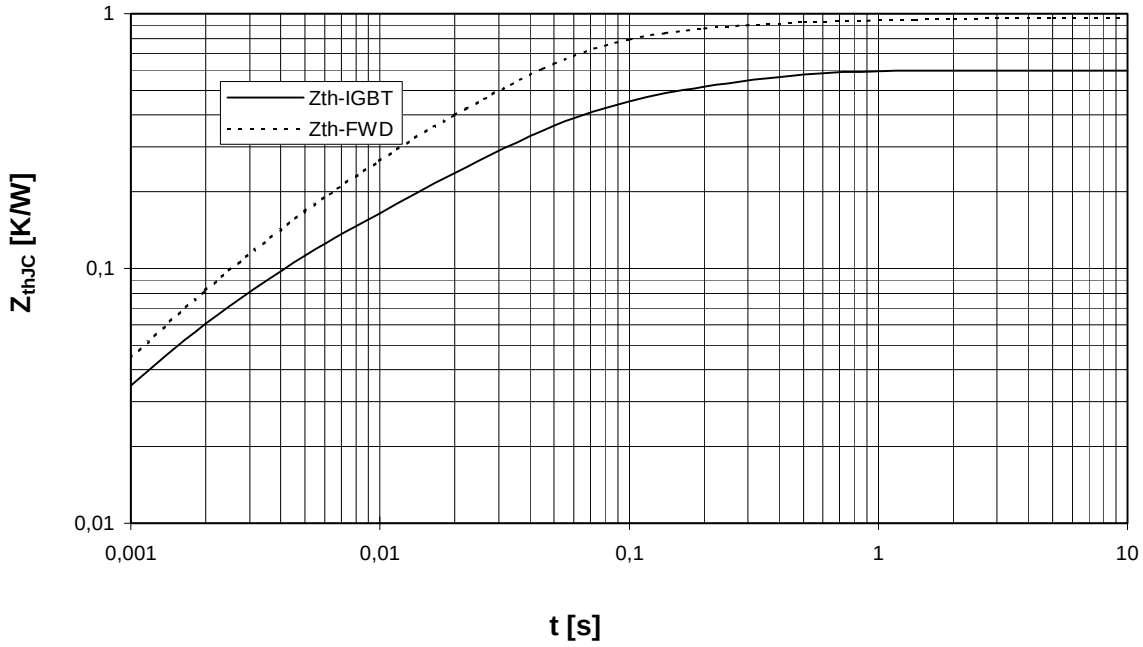


Schaltverluste Wechselr. (typisch) $E_{on} = f(R_G)$, $E_{off} = f(R_G)$, $E_{rec} = f(R_G)$
Switching losses Inverter (typical) T_j = 125°C, V_{GE} = +-15 V , $I_c = I_{nenn}$, V_{CC} = **600 V**

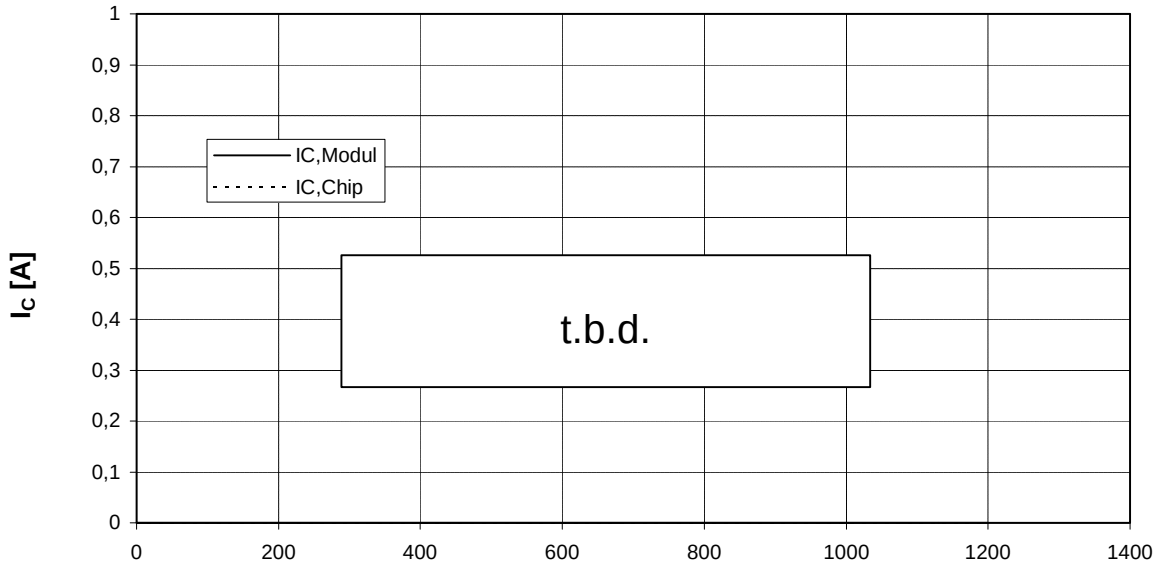


Vorläufige Daten
Preliminary data

Transienter Wärmewiderstand Wechselr. $Z_{thJC} = f(t)$
Transient thermal impedance Inverter



Sicherer Arbeitsbereich Wechselr. (RBSOA) $I_C = f(V_{CE})$
Reverse bias save operating area Inverter (RBSOA) T_{vj} = 125°C, V_{GE} = ±15V, R_G = 27 Ohm



Vorläufige Daten
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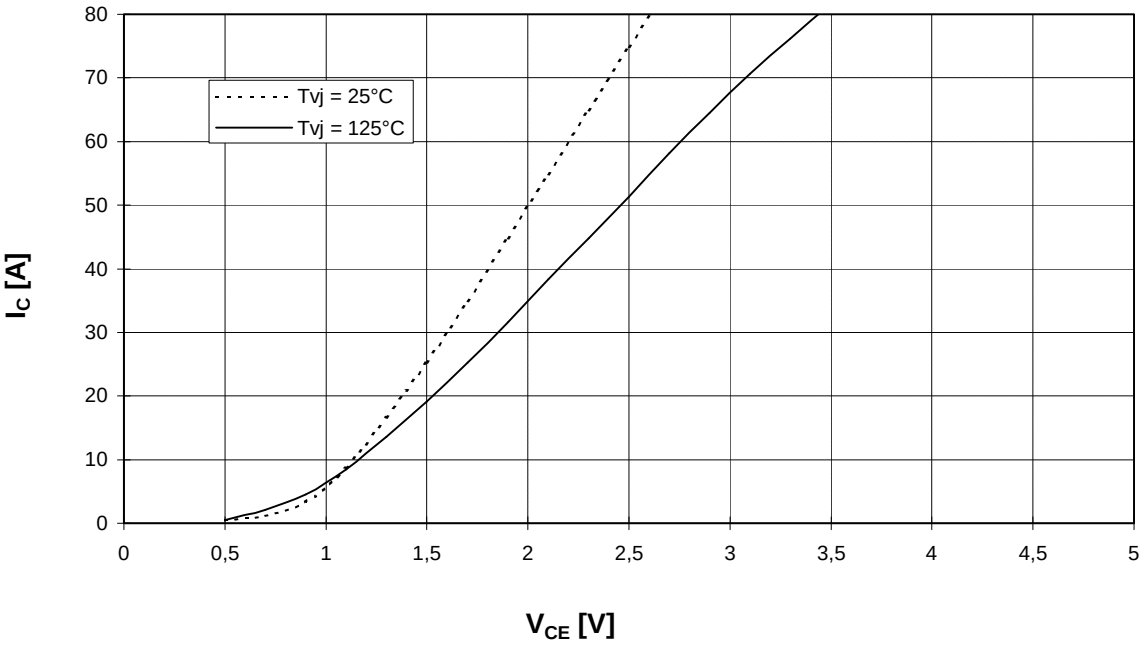
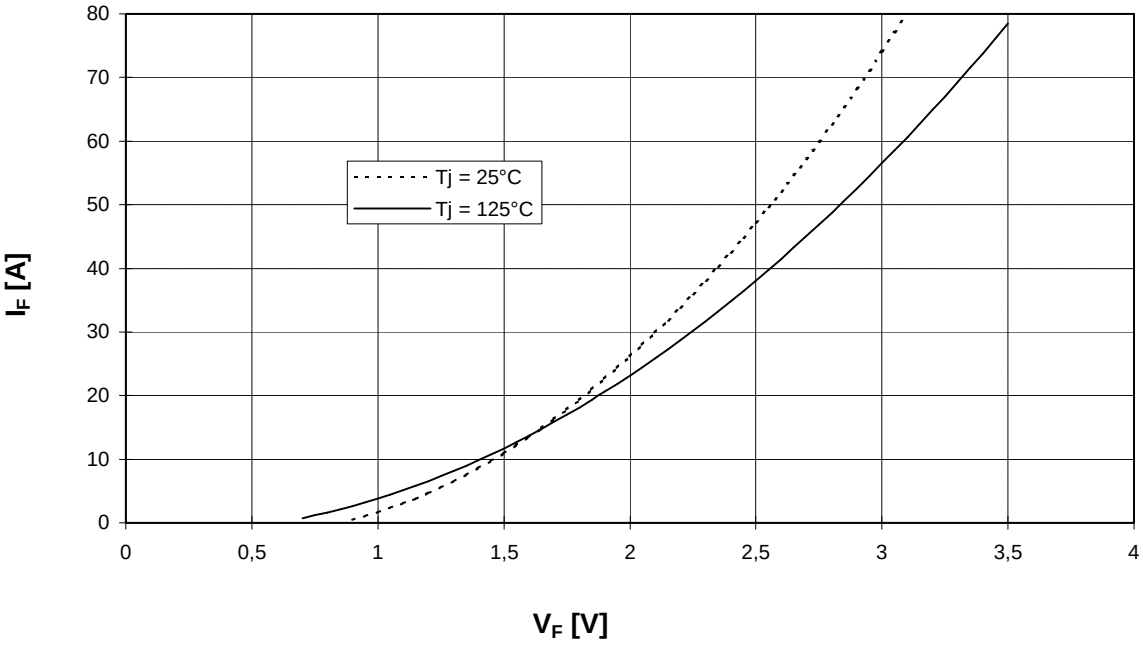
Ausgangskennlinienfeld Brems-Chopper-IGBT (typisch) $I_C = f(V_{CE})$
Output characteristic brake-chopper-IGBT (typical) $V_{GE} = 15\ V$



Durchlaßkennlinie der Brems-Chopper-Diode (typisch) $I_F = f(V_F)$
Forward characteristic of brake-chopper-FWD (typical)



Vorläufige Daten
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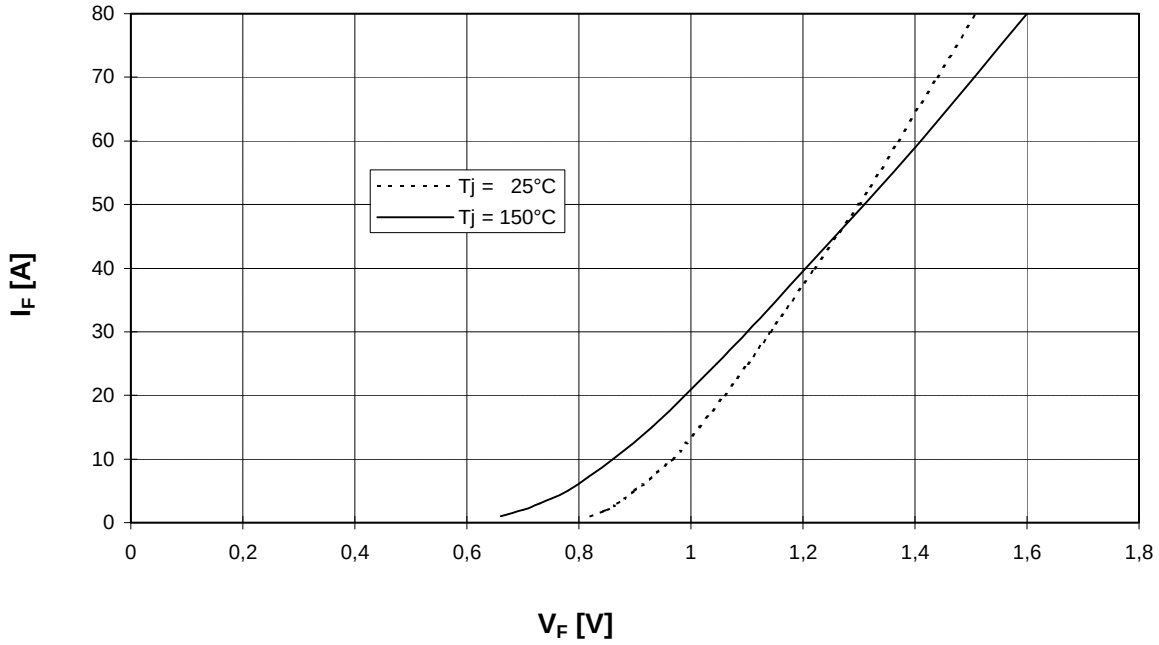
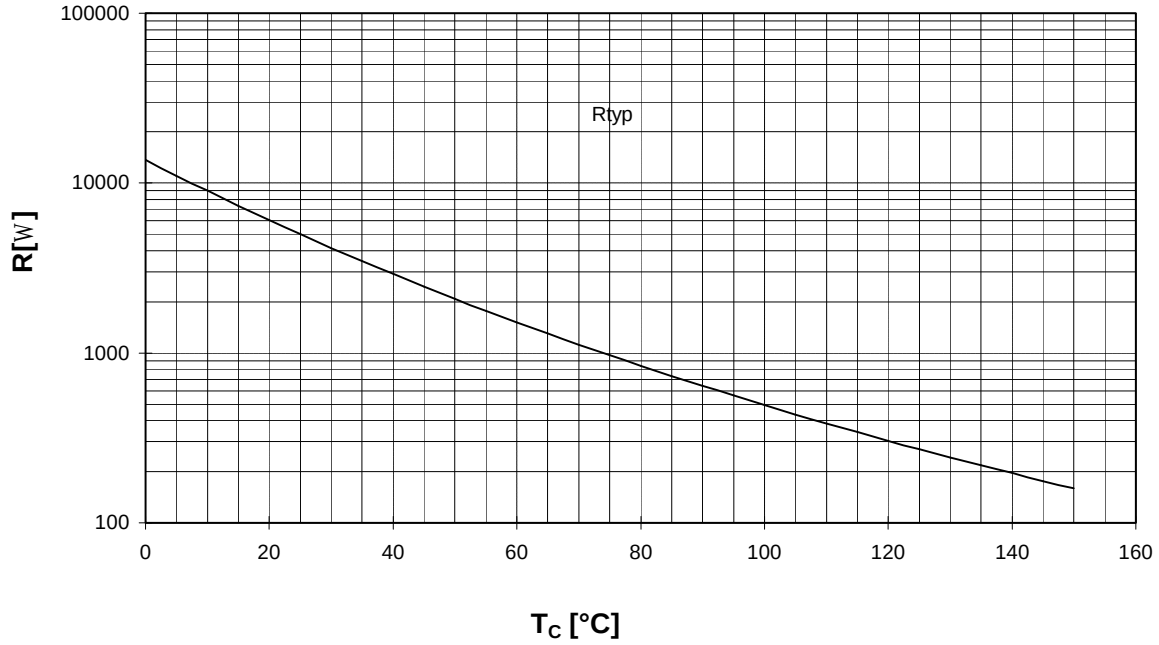
Durchlaßkennlinie der Gleichrichterdiode (typisch) $I_F = f(V_F)$
Forward characteristic of Rectifier Diode (typical)

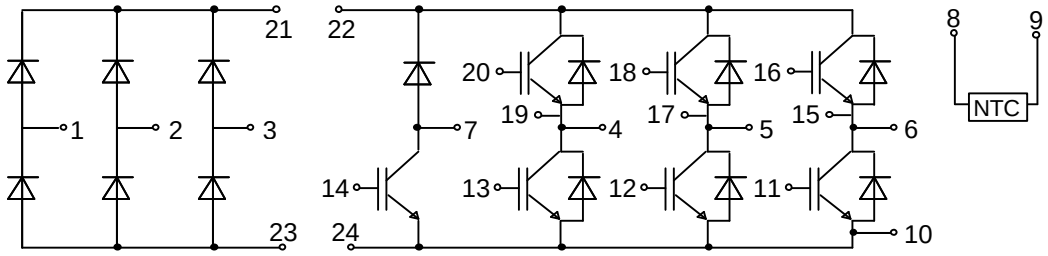


NTC- Temperaturkennlinie (typisch) $R = f(T)$
NTC- temperature characteristic (typical)

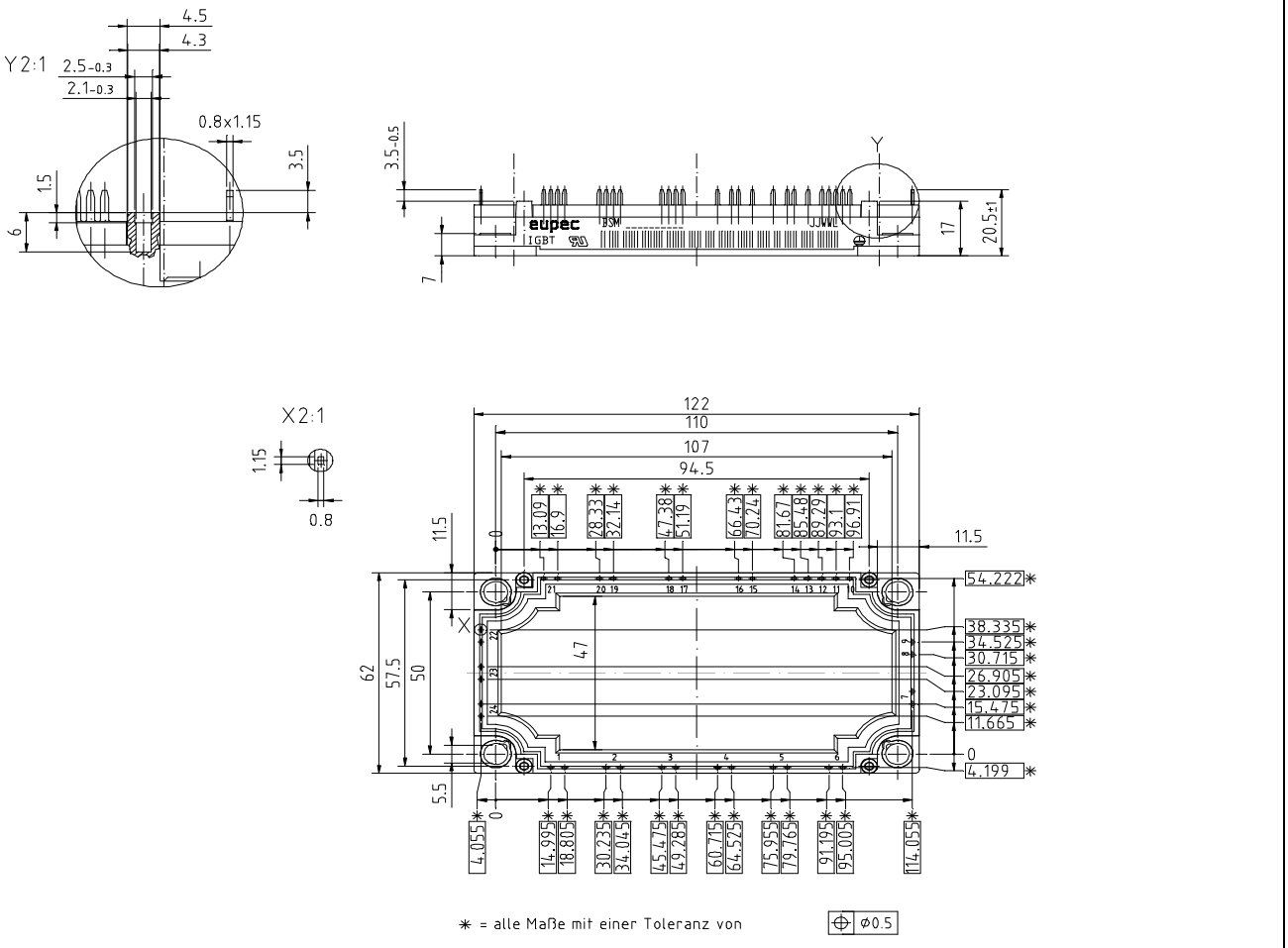


Vorläufige Daten
Preliminary data

Schaltplan/ Circuit diagram



Gehäuseabmessungen/ Package outlines



Mit dieser technischen Information werden Halbleiterbauelemente spezifiziert, jedoch keine Eigenschaften zugesichert. Sie gilt in Verbindung mit den zugehörigen Technischen Erläuterungen.

This technical information specifies semiconductor devices but promises no characteristics. It is valid in combination with the belonging technical notes.

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